



Progress on X-ray Imagers at MIT

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Acknowledgements

At MKI:

Gregory Prigozhin

Steve Kissel

Rick Foster

Bev LaMarr

At MIT Lincoln Laboratory:

Vyshi Suntharalingam

Barry Burke

Stephanie Hsu (now Stanford)

Kevin Ryu



Overview

- Near term: Directly-deposited blocking filters
- Far term: 3-D Active Pixel X-ray Sensors
- Mid term: Advanced CCDs



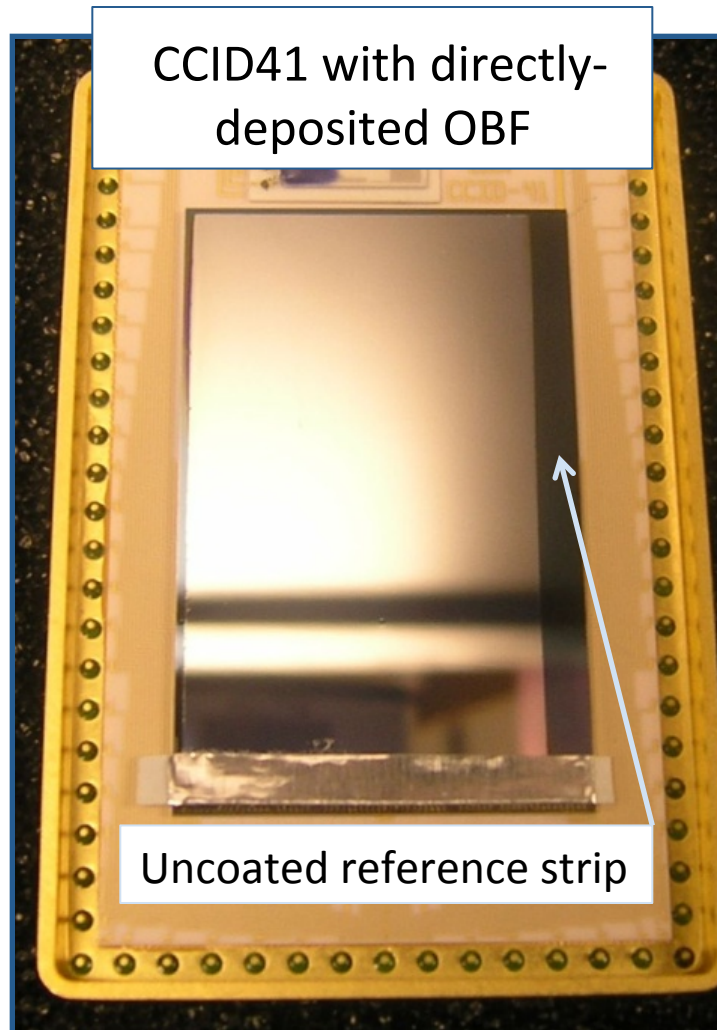
Deposited Filters: Objectives

- Avoid fragile optical/UV blocking filters, associated support hardware (e.g. vacuum doors), risk & I&T expense.
- Improve instrument performance





Status: 1st Coated BI CCD under test



- Chip-level coating process characterized in depth
- 1st test device: engineering grade with prior MBE BI treatment
- OBF: 220nm Al over 140nm 'buffer' layer
 - * Buffer reduces OBF-induced dark current
- Characterization in progress
 - * Soft X-ray QE confirms Al thickness
- Next:
 - * Thinner buffer layer on higher-quality device



Beyond CCDs: Active Pixel Sensors (APS)

- Faster readout → better QE, count-rate, timing
 - * Speed comes from parallelism & technology
 - * Parallelism comes from CMOS compatibility
- “No” charge transfer → better radiation tolerance
- Integrated signal/data processing
 - * Allows Gpix focal planes at kHz rates
 - * Allows for on-chip intelligence (e.g., event detection)



Challenges for APS in X-ray Astronomy

- Challenge for monolithic architectures: detection efficiency
 - * Difficult to deplete $\sim 100+$ μm
 - * May be difficult to tile large focal planes
- Challenge for hybrid architectures: noise
 - * Interlayer connection has large capacitance \rightarrow lower responsivity, higher noise (referred to input)
- Challenge for both: demonstrate proper BI treatment



MIT/Lincoln 3D X-ray Sensor (APS2)

Readout 'tier':

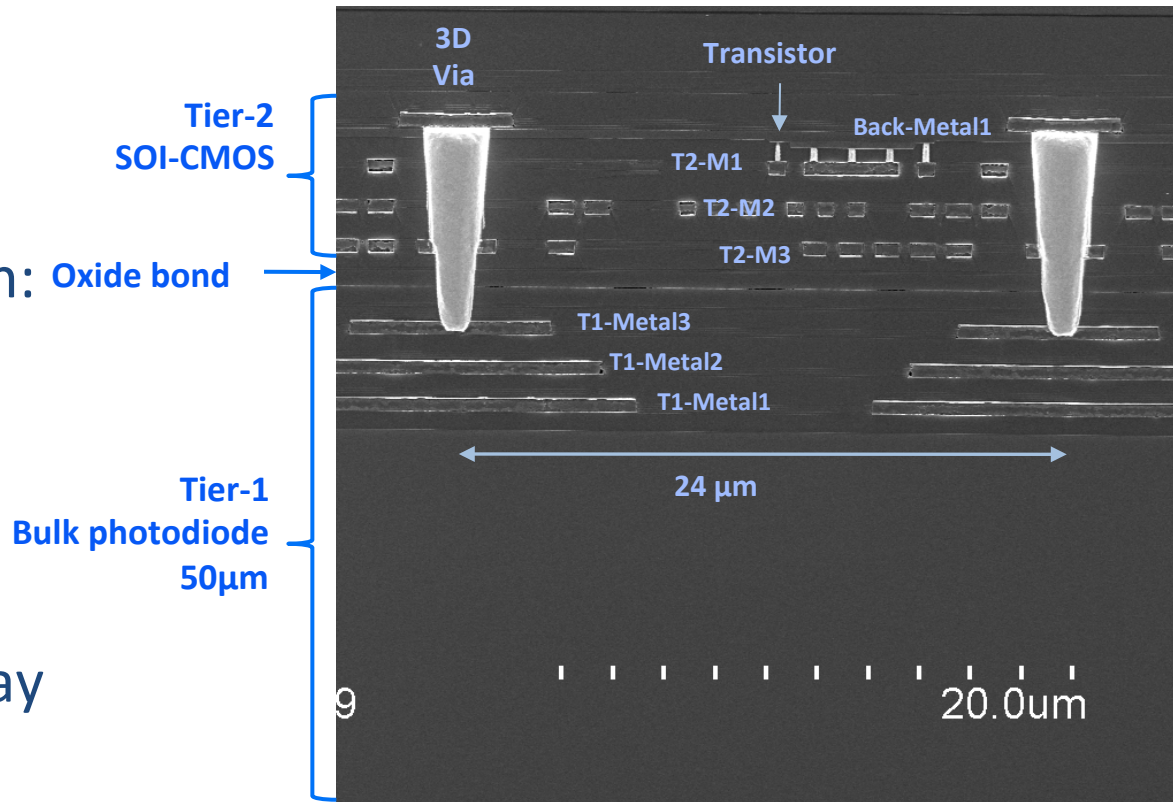
- * FDSOI CMOS
- * 350nm/3.3V

Inter-wafer connection: Oxide bond

- * Tungsten Via
- * Low-T oxide bond

Detector 'tier':

- * Bulk photodiode array
- * 3 k Ω -cm n-substrate
- * Thinned (50 μ m)
- * Back-illuminated

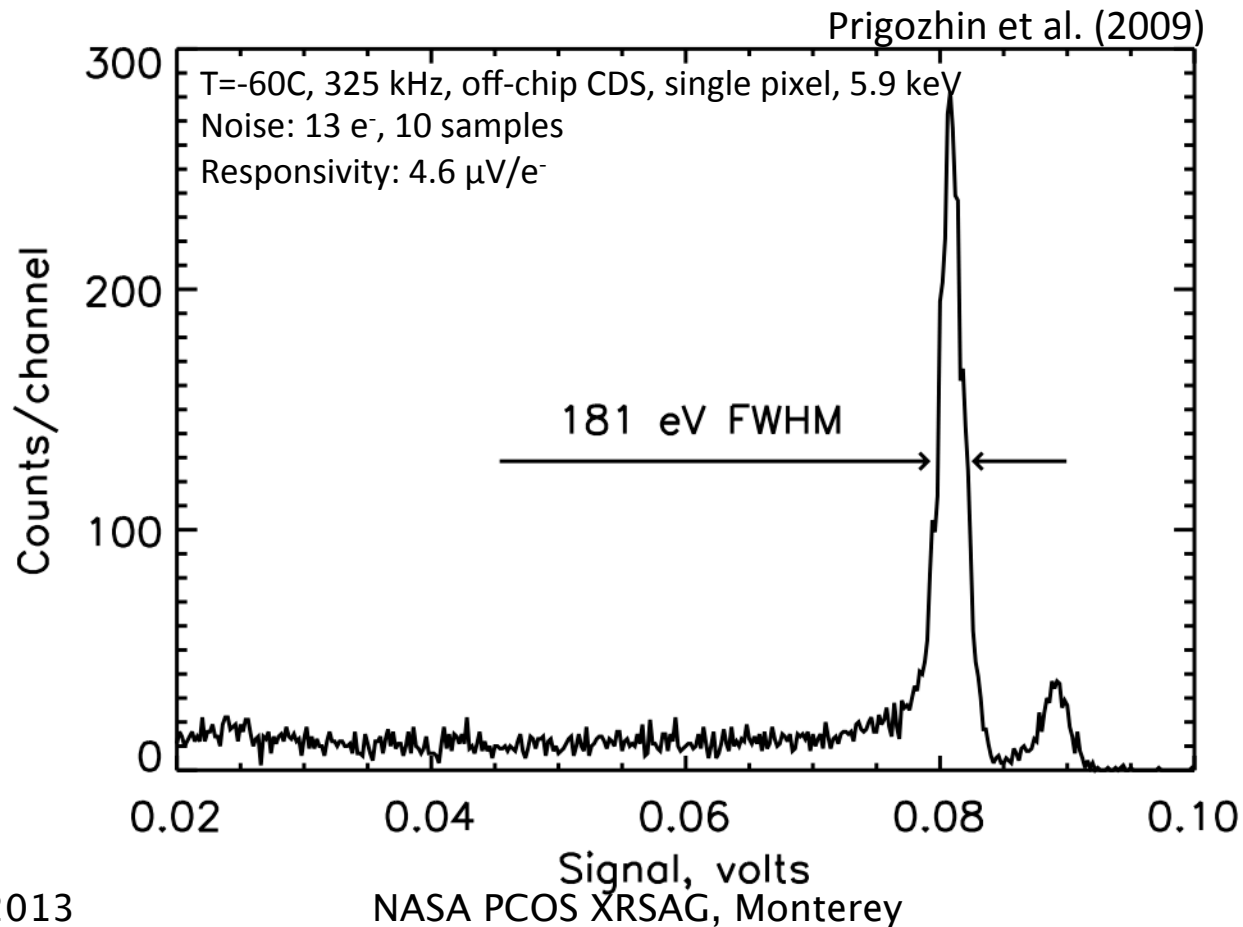


Test Array: V. Suntharalingam, MIT/LL
* 256 x 256, 24 μ m pixels



X-ray Performance at 5.9 keV

MIT/LL 3-D X-ray Active Pixel Sensor APS2





Next Generation Sensor APS3

Goals:

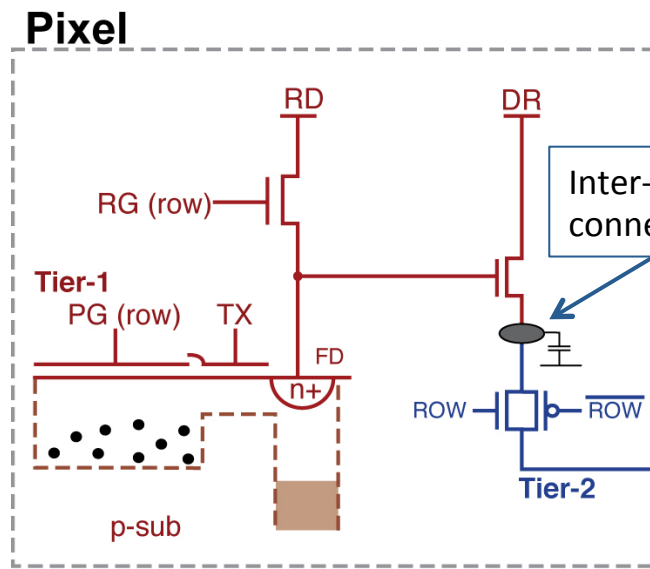
- * Reduce noise through improved responsivity, lower transistor noise
- * Reduce inter-pixel coupling through better layout
- * Demonstrate high-quality back-illumination (good soft X-ray response)



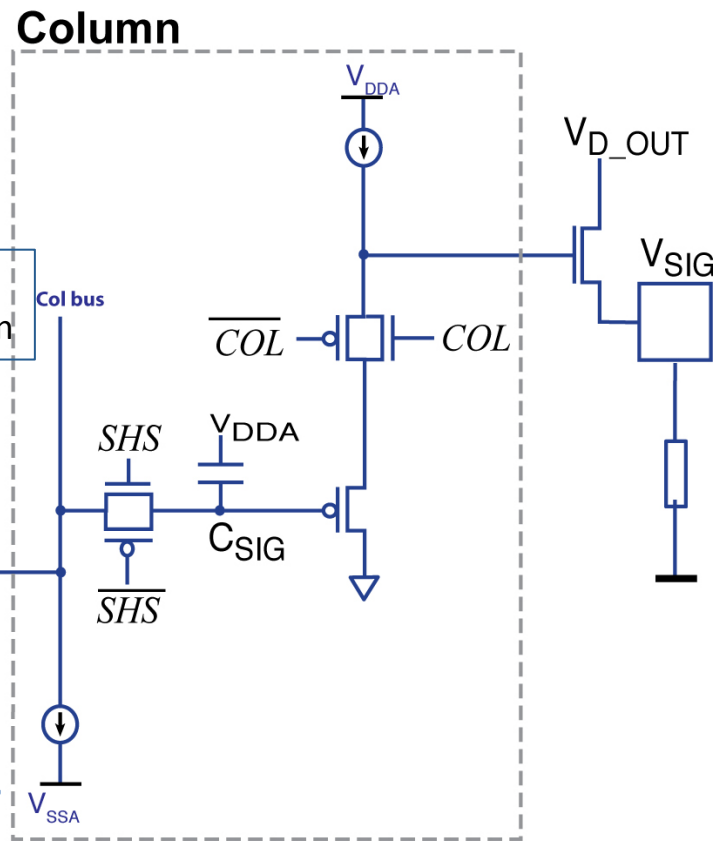
APS3 pixel with CCD-like output

Red:

In Detector Tier

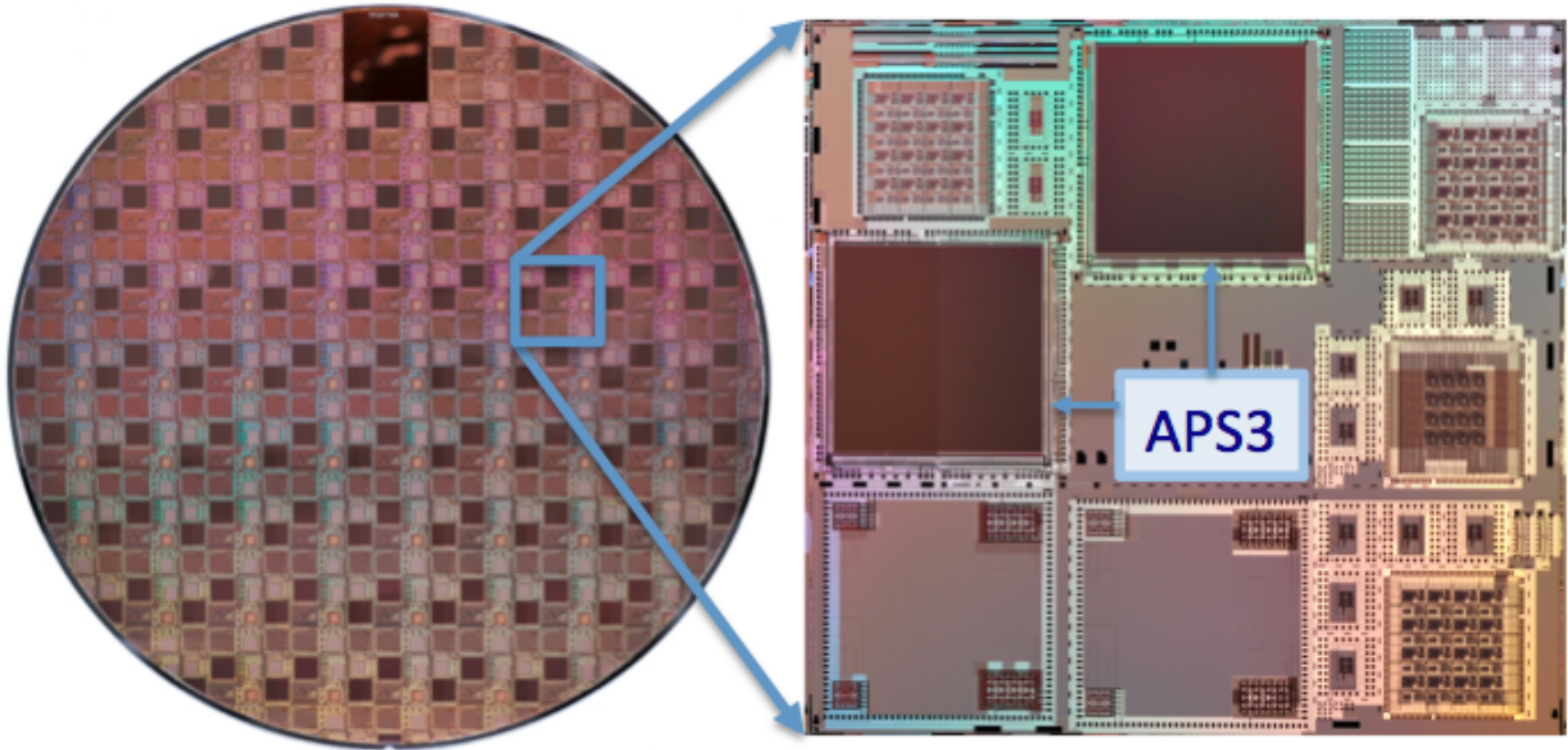


Blue:
In Readout Tier





APS3 CMOS Readout Tier



200mm-diameter wafer (45 die)

Shared, 22 mm die; 2 APS3 readouts



APS3 Status

- Expected performance:
 - ~ $<5 e^-$ noise; 50-100 μm depletion, back-illumination
- Status:
 - * Tier-2 complete; Tier-1 in fabrication
 - * Front-illuminated devices within ~ 6 months



Progress in CCD Technology: a middle way

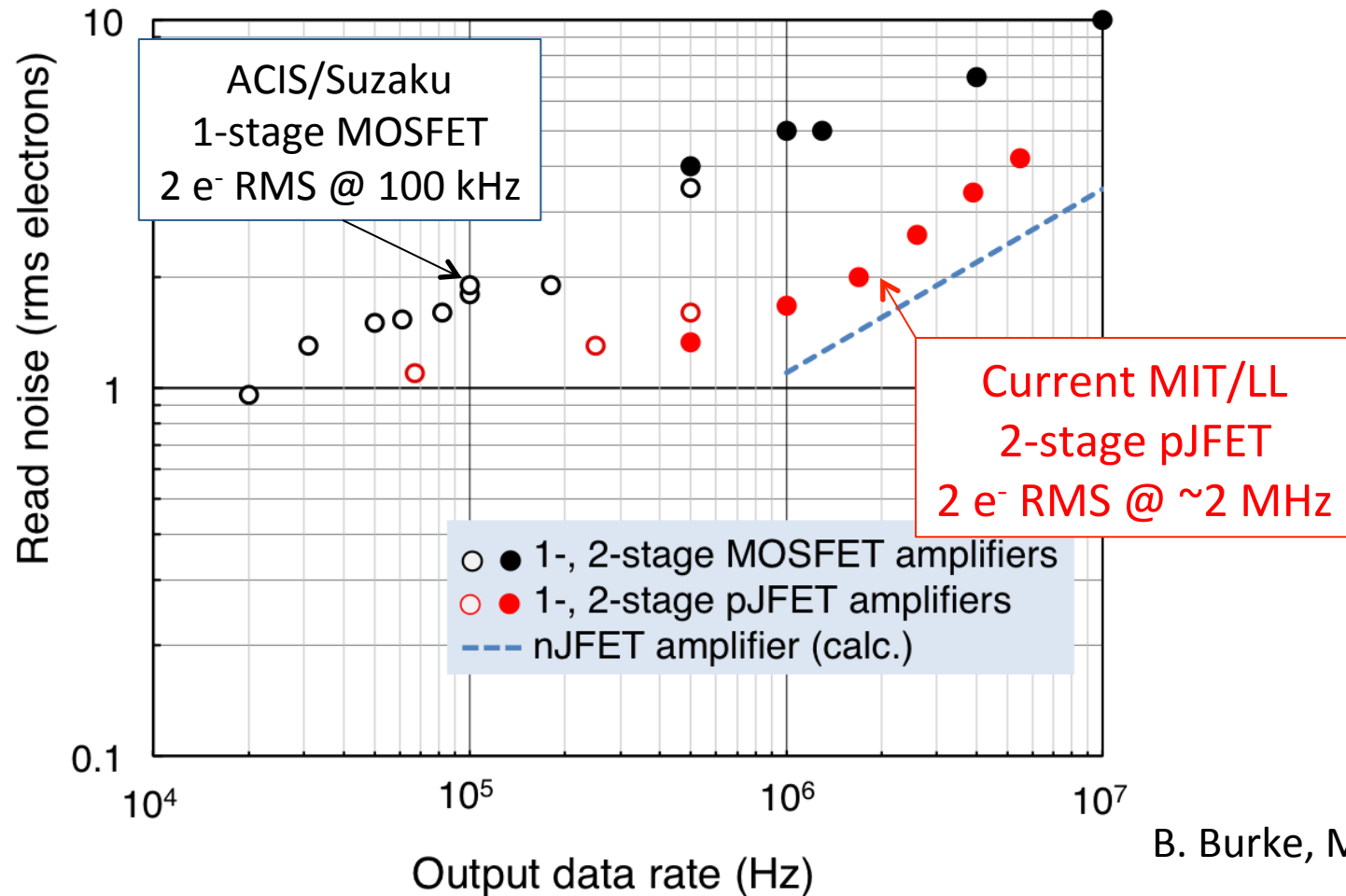
- CCD technology has advanced since Suzaku:
 - * Much faster readout at a given noise level
 - * Much lower power
 - * More flexible architecture for larger focal planes and better radiation tolerance
- These advances can meet near-term technology development needs, e.g., for
 - * Faster, low-power XGS readouts for AXSIO
 - * Large-area, wide-field detectors for Explorers



Advanced CCD Technology

from MIT Lincoln Laboratory

1. 10x faster low-noise output amplifiers



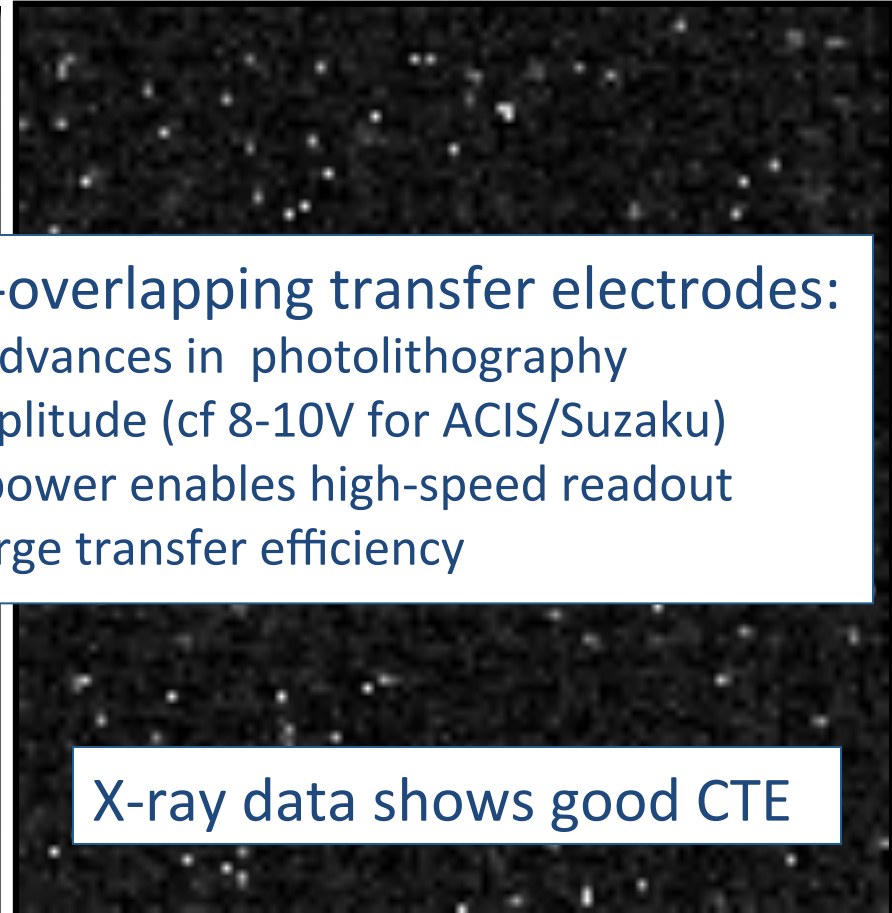
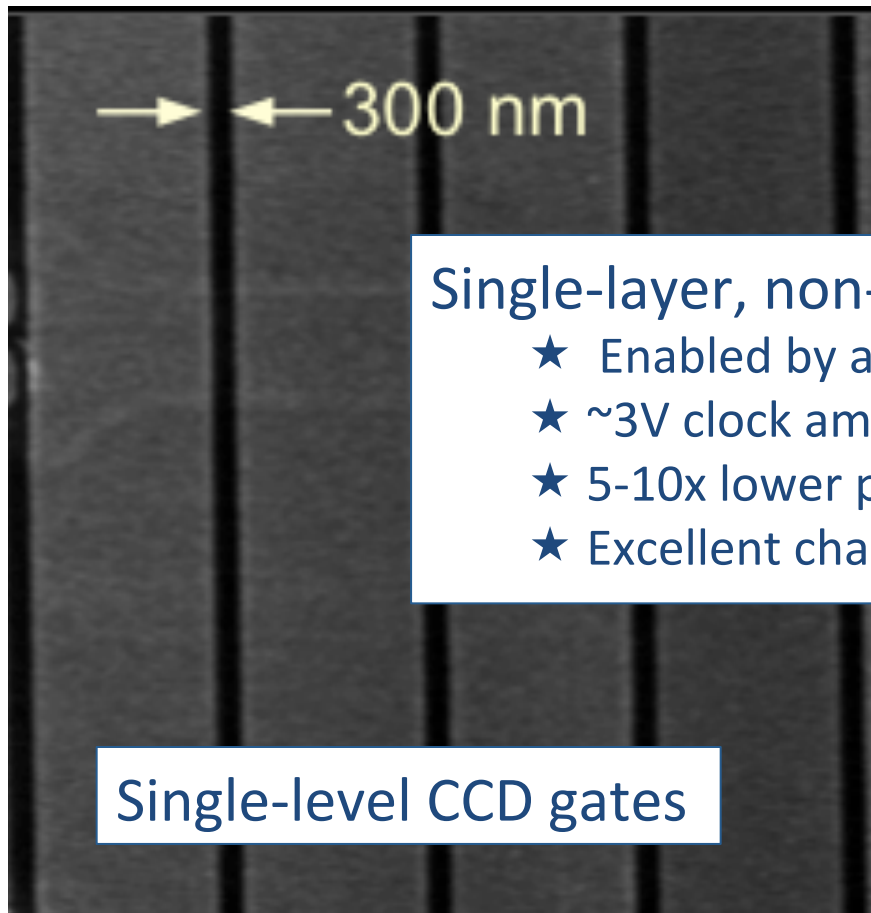
B. Burke, MIT/LL



Advanced CCD Technology

from MIT Lincoln Laboratory

2. Low-power, high-speed charge transfer



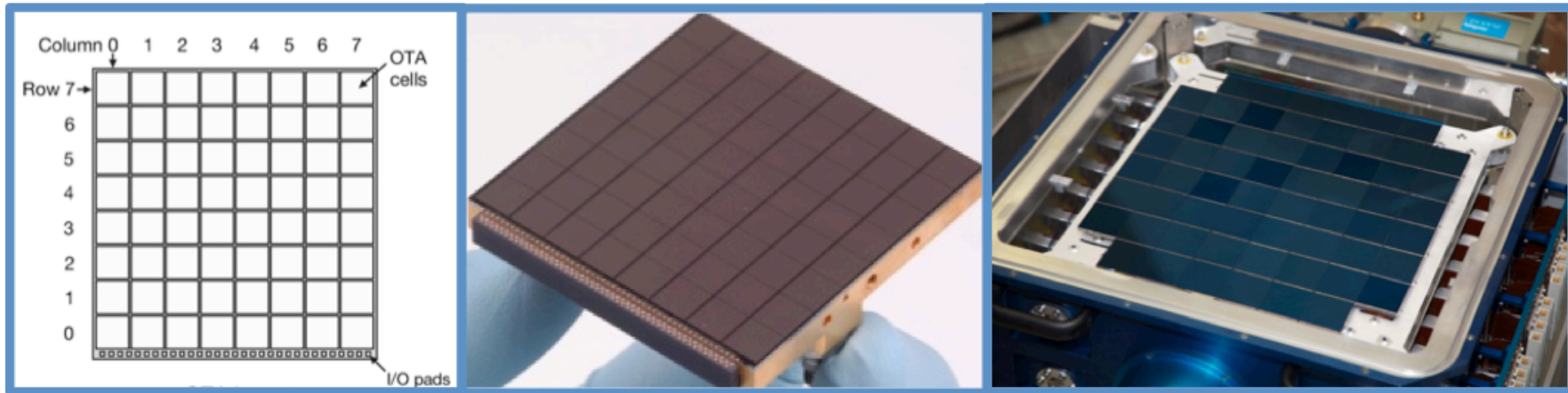
Single-layer, non-overlapping transfer electrodes:

- ★ Enabled by advances in photolithography
- ★ ~3V clock amplitude (cf 8-10V for ACIS/Suzaku)
- ★ 5-10x lower power enables high-speed readout
- ★ Excellent charge transfer efficiency



Advanced CCD Technology from MIT Lincoln Laboratory

3. Modular, multiplexed CCD architecture



Schematic:
8x8 CCD cells per chip

Pan-STARRS detector:
5x5 cm, ~4.8k x 4.8k pixels

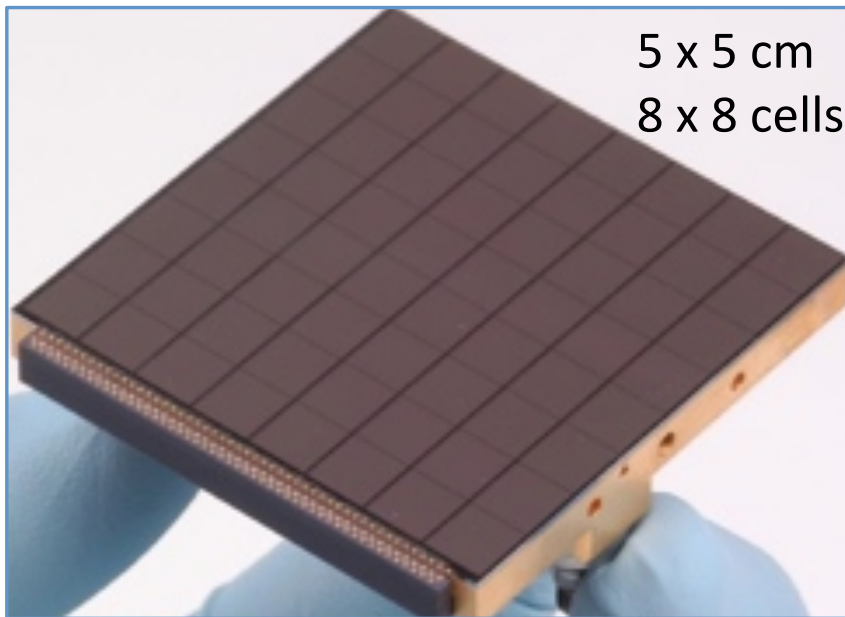
Pan-STARRS focal plane:
~400 x 400 mm

Developed for Pan-STARRS (Tonry, Burke+, 2008)

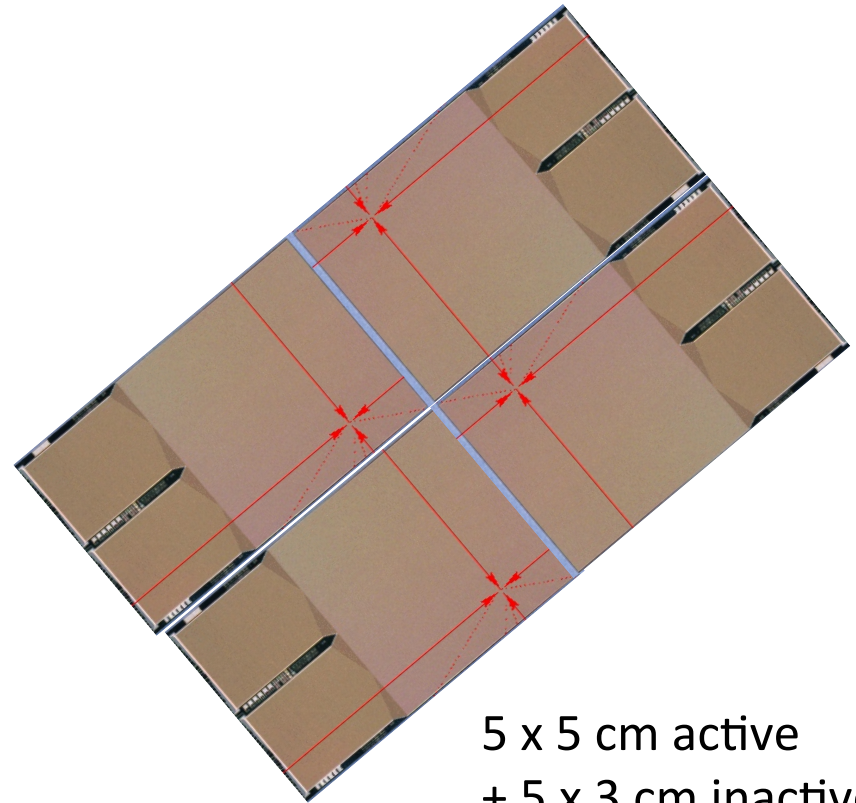
- ★ Allows large (5 x 5 cm) detectors w/ multiple CCDs (cells) on one chip
- ★ Multiple parallel outputs for higher speed readout
- ★ Four-side abutable to tile very large focal planes
- ★ Small cells minimize transfer distance, improve radiation tolerance
- ★ Modular: cells can be assembled in multiple configurations



Modular and ACIS/Suzaku CCDs



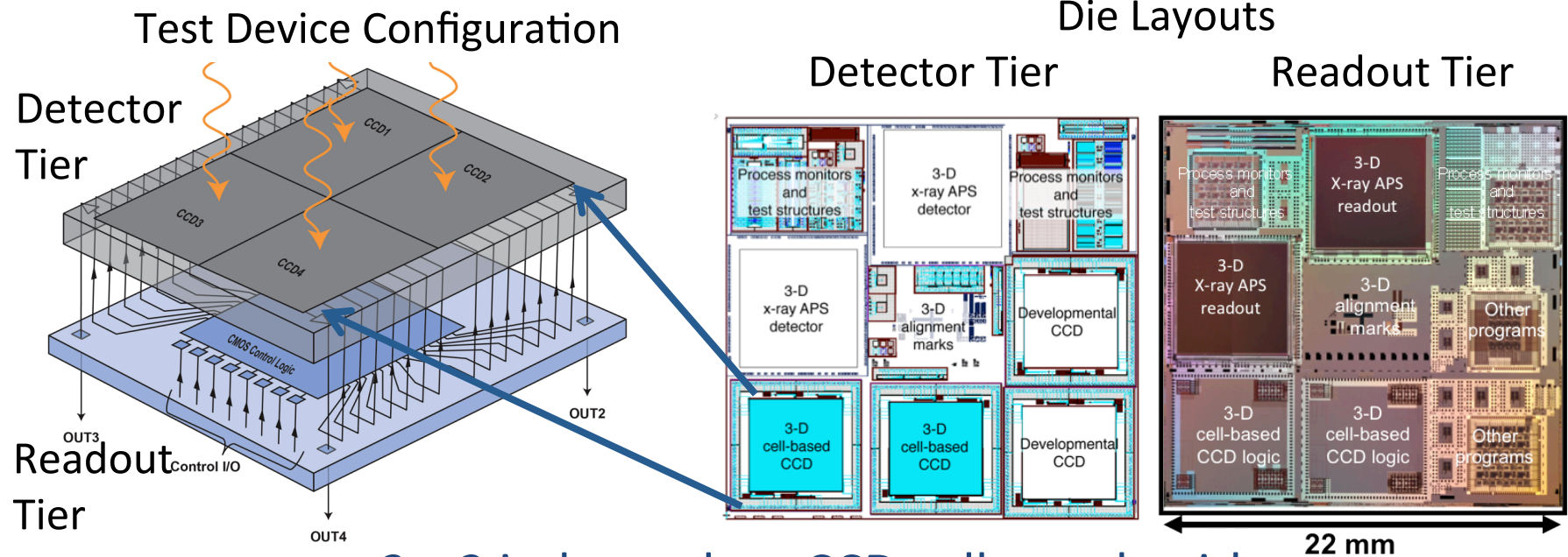
Pan-STARRS modular CCD



ACIS-I Focal Plane



Modular 3-D Advanced CCD Now in Fabrication at MIT/Lincoln



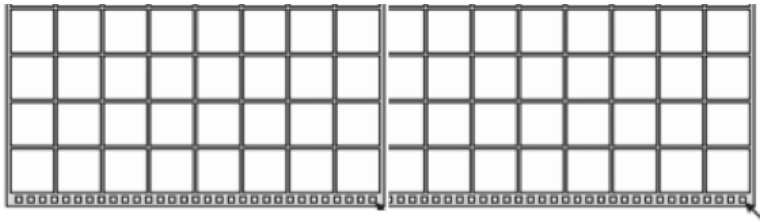
2 x 2 independent CCD cells, each with:

- 512 x 512 pixels, 4.8 μm square
- High-speed low-noise amplifiers
- High-speed, low-power transfer gates

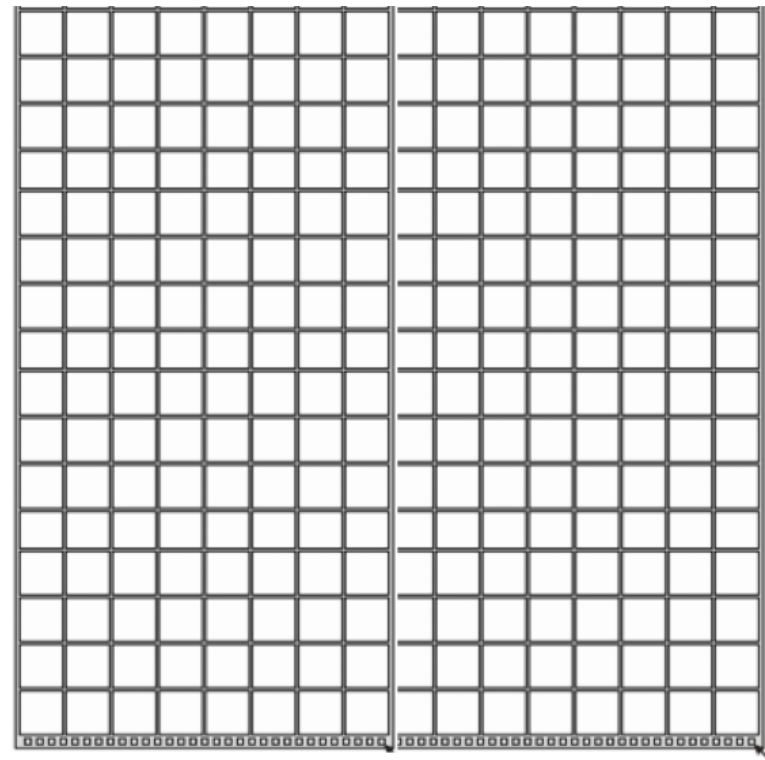


Modular Architecture Supports Multiple Applications

For X-ray Grating Spectrometer



For Wide-field Explorer

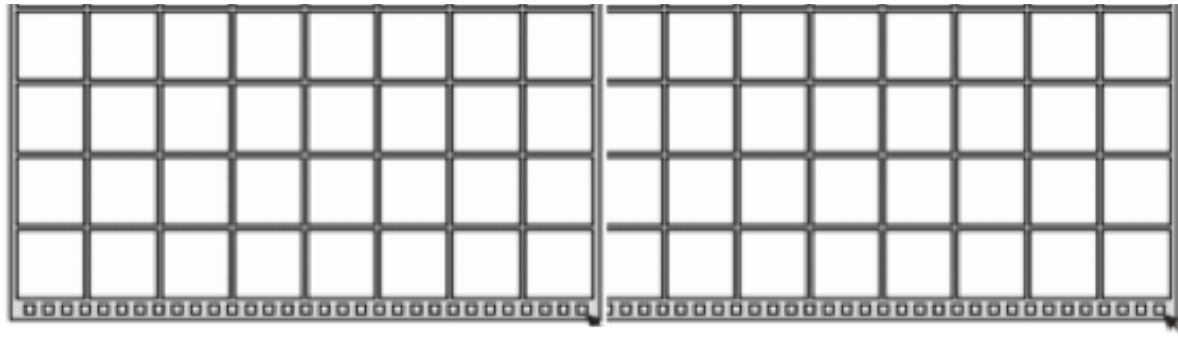


- Single CCD cell module design serves multiple applications
- Cell array tailored for each application
- Reduces design cost and risk, increases TRL



Modular Architecture Supports Multiple Applications

X-ray Grating Spectrometer Detector



- 4 x 16 independent CCD cells; 10 x 40 mm
- 15 Hz frame rate meets AXSIO requirement
- Power consumption 20% of Suzaku-based AXSIO XGS
- Electronics mass 25% of Suzaku-based AXSIO XGS
- Radiation tolerance 10x better than ACIS



Summary

- CCD technology continues to progress
- This progress offers important benefits to X-ray astronomy:
 - * Achieves performance requirements
 - * Reduces power & mass, increases reliability
- Effective technology development planning must allow for unplanned technical progress